

Supplemental Information

Mechanism of vertical Ge nanowire nucleation on Si (111) during sub-eutectic annealing and growth

Se Jun Park, Sung Hwan Chung, Bong Joong Kim, Minghao Qi, Xianfan Xu, Eric A. Stach,
and Chen Yang

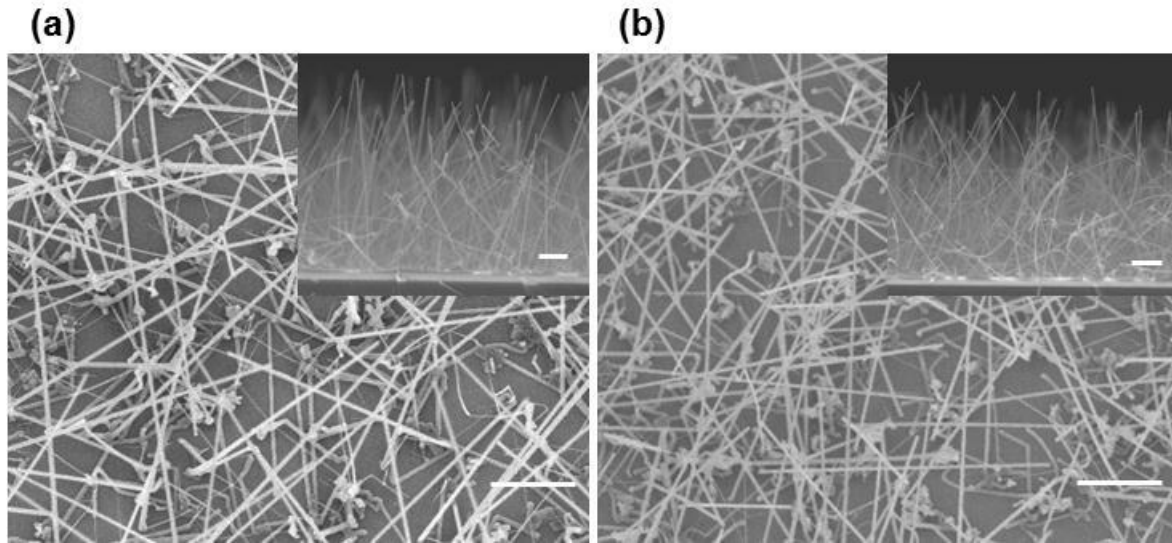


Figure S1: SEM images of Ge nanowires grown on the SiO₂ surface, with annealing at 320 °C (a) and 400 °C (b). SEM images were taken with a 25° inclination from the plan-view (in a, b and c) and in cross-sectional view (insets to a, b and c). All scale bars are 1 μm.